



SHEET 1 OF 13

| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(Substitute for form 1449/PTO) |          |                                                                                                                                                                                                                                                                 |                                | ATTY. DOCKET NO.<br><b>061282-0234</b>          |                                                                           | SERIAL NO.<br><b>10/574,863</b> |  |
|------------------------------------------------------------------------------------------------|----------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------|-------------------------------------------------|---------------------------------------------------------------------------|---------------------------------|--|
|                                                                                                |          |                                                                                                                                                                                                                                                                 |                                | APPLICANT<br><b>Yuichiro SASAKI, et al.</b>     |                                                                           |                                 |  |
|                                                                                                |          |                                                                                                                                                                                                                                                                 |                                | FILING DATE<br><b>April 06, 2006</b>            |                                                                           | GROUP<br><b>2823</b>            |  |
| <b>U.S. PATENT DOCUMENTS</b>                                                                   |          |                                                                                                                                                                                                                                                                 |                                |                                                 |                                                                           |                                 |  |
| EXAMINER'S INITIALS                                                                            | CITE NO. | Document Number<br>Number-Kind Code <sup>2</sup> (if known)                                                                                                                                                                                                     | Publication Date<br>MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |                                 |  |
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| EXAMINER'S INITIALS                                                                            | CITE NO. | Foreign Patent Document<br>Country Codes-Number & -Kind<br>Codes (if known)                                                                                                                                                                                     | Publication Date<br>MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines Where Relevant Figures Appear                       | Translation<br>Yes No           |  |
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| EXAMINER'S INITIALS                                                                            | CITE NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. |                                |                                                 |                                                                           |                                 |  |
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| /Phillip Green/                                                                                |          |                                                                                                                                                                                                                                                                 | EXAMINER                       |                                                 | DATE CONSIDERED                                                           |                                 |  |
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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /P.G./

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| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(Substitute for form 1449/PTO) |          |                                                                                                                                                                                                                                                                 |                                | ATTY. DOCKET NO.<br><b>061282-0234</b>          |                                                                           | SERIAL NO.<br><b>10/574,863</b> |    |
|------------------------------------------------------------------------------------------------|----------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------|-------------------------------------------------|---------------------------------------------------------------------------|---------------------------------|----|
|                                                                                                |          |                                                                                                                                                                                                                                                                 |                                | APPLICANT<br><b>Yuichiro SASAKI, et al.</b>     |                                                                           |                                 |    |
|                                                                                                |          |                                                                                                                                                                                                                                                                 |                                | FILING DATE<br><b>April 06, 2006</b>            |                                                                           | GROUP<br><b>2823</b>            |    |
| <b>U.S. PATENT DOCUMENTS</b>                                                                   |          |                                                                                                                                                                                                                                                                 |                                |                                                 |                                                                           |                                 |    |
| EXAMINER'S INITIALS                                                                            | CITE NO. | Document Number<br>Number-Kind Code <sup>2</sup> (if known)                                                                                                                                                                                                     | Publication Date<br>MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |                                 |    |
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|                                                                                                |          |                                                                                                                                                                                                                                                                 |                                |                                                 |                                                                           | Yes                             | No |
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| <b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>                        |          |                                                                                                                                                                                                                                                                 |                                |                                                 |                                                                           |                                 |    |
| EXAMINER'S INITIALS                                                                            | CITE NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. |                                |                                                 |                                                                           |                                 |    |
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| /Phillip Green/ EXAMINER                                                                       |          |                                                                                                                                                                                                                                                                 |                                | 06/26/2008 DATE CONSIDERED                      |                                                                           |                                 |    |

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|                                                                                                |             |                                                                                                                                                                                                                                                                 |                                | APPLICANT<br><b>Yuichiro SASAKI, et al.</b>        |                                                                                 |                                            |  |
|                                                                                                |             |                                                                                                                                                                                                                                                                 |                                | FILING DATE<br><b>April 6, 2006</b>                |                                                                                 | GROUP<br><b>2823</b>                       |  |
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| EXAMINER'S<br>INITIALS                                                                         | CITE<br>NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. |                                |                                                    |                                                                                 |                                            |  |
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| EXAMINER<br>/Phillip Green/                                                                    |             |                                                                                                                                                                                                                                                                 |                                | DATE CONSIDERED<br>06/26/2008                      |                                                                                 |                                            |  |

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| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(Substitute for form 1449/PTO) |          |                                                                                                                                                                                                                                                                          |                                | ATTY. DOCKET NO.<br><b>061282-0234</b>          |  | SERIAL NO.<br><b>Serial No. 10/574,863</b>                                |  |
|                                                                                                |          |                                                                                                                                                                                                                                                                          |                                | APPLICANT<br><b>Yuichiro SASAKI, et al.</b>     |  |                                                                           |  |
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|                                                                                                |          | US                                                                                                                                                                                                                                                                       |                                |                                                 |  |                                                                           |  |
| OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)                               |          |                                                                                                                                                                                                                                                                          |                                |                                                 |  |                                                                           |  |
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| /Phillip Green/                                                                                |             | EXAMINER                                                                                                                                                                                                                                                                        |                                | DATE CONSIDERED                                    |                                                                                 |
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|                                                                                                |             |                                                                                                                                                                                                                                                                 |                                |                                                    |                                                                                 |
|------------------------------------------------------------------------------------------------|-------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------|----------------------------------------------------|---------------------------------------------------------------------------------|
| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(Substitute for form 1449/PTO) |             | ATTY. DOCKET NO.<br><b>061282-0234</b>                                                                                                                                                                                                                          |                                | SERIAL NO.<br><b>Serial No. 10/574,863</b>         |                                                                                 |
|                                                                                                |             | APPLICANT<br><b>Yuichiro SASAKI, et al.</b>                                                                                                                                                                                                                     |                                |                                                    |                                                                                 |
|                                                                                                |             | FILING DATE<br><b>April 6, 2006</b>                                                                                                                                                                                                                             |                                | GROUP<br><b>2823</b>                               |                                                                                 |
| <b>U.S. PATENT DOCUMENTS</b>                                                                   |             |                                                                                                                                                                                                                                                                 |                                |                                                    |                                                                                 |
| EXAMINER'S<br>INITIALS                                                                         | CITE<br>NO. | Document Number<br>Number-Kind Code <sup>2</sup> (if known)                                                                                                                                                                                                     | Publication Date<br>MM-DD-YYYY | Name of Patentee or Applicant of Cited<br>Document | Pages, Columns, Lines, Where<br>Relevant Passages or Relevant<br>Figures Appear |
| OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)                               |             |                                                                                                                                                                                                                                                                 |                                |                                                    |                                                                                 |
| EXAMINER'S<br>INITIALS                                                                         | CITE<br>NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. |                                |                                                    |                                                                                 |
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| EXAMINER<br>/Phillip Green/                                                                    |             |                                                                                                                                                                                                                                                                 | DATE CONSIDERED<br>06/26/2008  |                                                    |                                                                                 |

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